

**AMENDMENTS TO THE SPECIFICATION:**

On page 1, line 1, please delete "DESCRIPTION"

On page 1, line 2, please insert the following heading:

"TITLE OF THE INVENTION"

On page 1, line 4, please insert the following heading:

"BACKGROUND OF THE INVENTION"

On page 2, line 27, please insert the following heading:

"BRIEF SUMMARY OF THE INVENTION"

On page 4, line 1, please insert the following heading:

"BRIEF DESCRIPTION OF THE SEVERAL VIEWS OF THE DRAWINGS"

On page 4, line 11, please insert the following heading:

"DETAILED DESCRIPTION OF THE INVENTION"

After page 11, please insert new page:

"ABSTRACT

A polycrystalline silicon GOLDD TFT with a gate overlying its channel is fabricated by using the gate as a mask during a first dopant implantation step. Spacers are then formed adjacent to the gate, which comprise portions of a thin metallic layer which are defined by fillets in an etching process. The spacers and gate are then used as a mask for doping source and drain regions, thereby providing a self-aligned fabrication technique."